

**In the Specification:**

Please amend the paragraph starting on page 8, line 24 as follows:

Fig. 4 is Fig. 5 is a graph illustrating a thickness of a dielectric film according to a deposition thickness of a thin film having a high dielectric constant.

Please amend the paragraph starting on page 12, line 7 as follows:

Preferably, the Al-rich HfO<sub>2</sub>-Al<sub>2</sub>O<sub>3</sub> film 47 and the Hf-rich HfO<sub>2</sub>-Al<sub>2</sub>O<sub>3</sub> film 49 have a thickness ranging from 5 to 30Å and 10 to 100Å, respectively, and formed according to an ALD process. Specifically, the ALD process is performed at a temperature ranging from 150 to 600°C using Al(CH<sub>3</sub>)<sub>3</sub> Al(CH<sub>4</sub>)<sub>3</sub> as an Al source, HfCl<sub>4</sub> as a Hf source and H<sub>2</sub>O as an O source. One cycle of Al<sub>2</sub>O<sub>3</sub> comprises Al pulse, N<sub>2</sub> purge, H<sub>2</sub>O pulse and N<sub>2</sub> purge processes, and one cycle of HfO<sub>2</sub> comprises Hf pulse, N<sub>2</sub> purge, H<sub>2</sub>O pulse and N<sub>2</sub> purge processes.

Please amend the paragraph starting on page 12, line 16 as follows:

In addition, the Hf source may be selected from the group consisting of HfCl<sub>4</sub>, Hf[N(C<sub>2</sub>H<sub>5</sub>)<sub>2</sub>]<sub>4</sub>, Hf[N(CH<sub>3</sub>)<sub>2</sub>]<sub>4</sub> HF[N(CH<sub>3</sub>)<sub>2</sub>]<sub>4</sub>, Hf[N(CH<sub>3</sub>)(C<sub>2</sub>H<sub>5</sub>)]<sub>4</sub>, Hf[OC(CH<sub>3</sub>)<sub>3</sub>]<sub>4</sub>, Hf(NO<sub>3</sub>)<sub>4</sub>, and combinations thereof, the O source may be selected from the group consisting of H<sub>2</sub>O, O<sub>2</sub>, N<sub>2</sub>O, O<sub>3</sub>, and combinations thereof, and one cycle of HfO<sub>2</sub> may comprise Hf pulse, N<sub>2</sub> purge, O pulse and N<sub>2</sub> purge.

Please amend the paragraph starting on page 13, line 15 as follows:

Fig. 4 is Fig. 5 is a graph illustrating a thickness of the dielectric films according to a deposition thickness of a thin film of the present invention and the conventional arts. As shown in Fig. 4 Fig. 5, the HfO<sub>2</sub>-Al<sub>2</sub>O<sub>3</sub> film of the invention has a smaller thickness.